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富士フイルム (各田南)

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# 2/ 8

## PATENT APPLICATION

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Kenichiro Sato et al.

Group Art Unit: 1752

Appl. No.: 09/834,639

Examiner: THORNTON, YVETTE C

Filed: April 16, 2001

For: POSITIVE PHOTORESIST COMPOSITION

DECLARATION UNDER 37 C.F.R. §1.132Assistant Commissioner for Patents  
Alexandria, VA 22313-1450

Sir:

I, Kenichiro Sato, do declare and state as follows:

I am a citizen of Japan.

I graduated from Osaka University, Faculty of Engineering, Course of  
Applied Fine Chemistry in March 1992.Since April 1992 I have been employed by Fuji Photo Film Co., Ltd. and  
have been engaged in research and development of photoresist photosensitive  
materials for semiconductors at the Yoshida-Minami Factory Research Division of  
the company.I am a co-inventor of the invention described and claimed in the  
above-named application, and I am familiar with the subject matter disclosed by the  
application.In order to demonstrate the unexpected superiority of the present  
invention, the following experimentation was conducted by me or under my  
supervision.

04- 3- 2: 6:34PM: NGB 特許部

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# 3/ 8

Page 2

PATENT APPLICATION

**EXPERIMENTATION****EXAMPLES A-1 TO F-4 AND COMPARATIVE EXAMPLES a-1 TO f-4**

Positive photoresist compositions using the resin and the photo-acid generator, and if necessary, the surface active agent and the basic compound, which are set forth in Table C below were prepared in the same manner as in Examples 2-1 to 2-18 of the present specification.

In Table C, Resins (2-1), (2-2), (2-3) and (2-9) are the resins described in the present specification, respectively. PAG4-50 is the compound described on page 80 of the present specification, and W-4 (polyoxyethylene nonylphenyl ether: a surfactant other than a fluorine-type and silicon-type surfactant) and W-5 (silicon-type surfactant, Troysol S-366, a product of Troy Chemical K. K.) are surfactants described on page 124 of the present specification. The Polymers (34) and (35), PAG 1, PGMEA, FC-430 (Fluorine-type surfactant) and tributylamine are compounds described in U.S.P. 6,280,898 (Hasegawa).

The positive photoresist compositions were evaluated on Edge Roughness (ER) and Number of Developing Defects in the same manner as in Examples 2-1 to 2-18 of the present specification. The results are shown in Table C below.

Page 3

## PATENT APPLICATION

TABLE C

	Resin	Acid Generator	Solvent	Surfactant	Organic Basic Compound	LIR	Number of Development Defects
Example A-1	2-1	PAG 4-50	PCMA	None	None	18 nm	170
A-2	2-2					18 nm	160
A-3	2-3					19 nm	165
A-4	2-9					19 nm	160
Comparative Example a-1	(35)	PAG 1	PCMA	None	None	35 nm	8620
a-2	(35)					36 nm	24040
a-3	(34)					37 nm	34120
a-4	(34)					36 nm	35410
Example B-1	2-1	PAG 4-50	PCMA	W-5	None	16 nm	80
B-2	2-2					16 nm	75
B-3	2-3					16 nm	88
B-4	2-9					16 nm	72
Comparative Example b-1	(35)	PAG 1	PCMA	W-5	None	30 nm	3520
b-2	(35)					29 nm	2910
b-3	(34)					30 nm	3710
b-4	(34)					30 nm	2990

Page 4

## PATENT APPLICATION

TABLE C (continued)

Example C-1	2-1	PAG 4-50	PCMEA	W-4	None	18 nm	120
C-2	2-2					17 nm	105
C-3	2-3					18 nm	115
C-4	2-9					18 nm	112
Comparative Example c-1	(35)	PAG 1	PCMEA	W-4	None	35 nm	5540
c-2	(35)					34 nm	4970
c-3	(34)					34 nm	5220
c-4	(34)					33 nm	4945
Example D-1	2-1	PAG 4-50	PCMEA	FC 430	None	16 nm	78
D-2	2-2					16 nm	74
D-3	2-3					17 nm	83
D-4	2-9					16 nm	70
Comparative Example d-1	(35)	PAG 1	PCMEA	FC 430	None	30 nm	3410
d-2	(35)					29 nm	2970
d-3	(34)					30 nm	2740
d-4	(34)					30 nm	2890

Page 5

PATENT APPLICATION

TABLE C (continued)

Example E-1	2-1	PAG 1	PCMEA	None	Tributylamine	15 nm	75
E-2	2-1					12 nm	35
E-3	2-1					15 nm	87
Comparative Example e-1	(35)	PAG 4-50	PCMEA	None	Tributylamine	28 nm	2830
e-2	(34)					26 nm	2460
e-3	(35)					28 nm	2710
Example F-1	2-1	PAG 1	PCMEA	FC 430	Tributylamine	12 nm	38
F-2	2-2					14 nm	65
F-3	2-3					12 nm	40
F-4	2-9	PAG 4-50	PCMEA	FC 430	Tributylamine	12 nm	35
Comparative Example f-1	(35)					20 nm	1290
Comparative Example f-2	(35)					25 nm	2320
Example f-3	(34)	PAG 1	PAG 4-50			21 nm	1170
Comparative Example f-4	(34)					27 nm	2290

Page 6

## PATENT APPLICATION

As is evident from the comparison of Additional Examples A-1 to A-4 with Comparative Examples a-1 to a-4, the feature of the present invention can be seen that specific effects can be obtained as regards LER and development defect owing to the use of a resin having a specific structure even for systems not containing any surfactant or organic basic compound.

In addition, in Additional Examples B-1 to B-4 with Comparative Examples b-1 to b-4, Additional Examples C-1 to C-4 with Comparative Examples c-1 to c-4, and Additional Examples D-1 to D-4 with Comparative Examples d-1 to d-4, advantageous effects of the present invention are not attained with use of Resin (34) or (35) set forth in cited reference Hasegawa. For confirmation, when those systems each containing a surfactant are compared with Examples of Additional Examples A-1 to A-4, it is apparent that still more preferable results are attained concerning LER and development defect due to the addition of a surfactant. (However, the surfactant is not an essential ingredient, but one used for preferable embodiments for the present invention.)

Moreover, by comparing Additional Example E-1 with Comparative Example e-1, or Additional Examples E-2 and E-3 with Comparative Examples e-2 and e-3, it is confirmed that the addition of an organic basic compound also gives more preferable results concerning LER and development defect.

As has been discussed heretofore, the present invention achieved unexpected excellent effects by introducing a specific resin, and is not obvious in view of the cited reference which specifically discloses nothing about the resin having the specific structure.

Page 7

## PATENT APPLICATION

I declare further that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under §1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Respectively submitted,

Date: March 2, 2004Kenichiro Sato

Kenichiro Sato